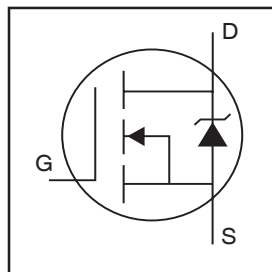


IRF3205PbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



$V_{DSS} = 55V$
$R_{DS(on)} = 8.0m\Omega$
$I_D = 110A^{\textcircled{5}}$

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	110 $\textcircled{5}$	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	80	
I_{DM}	Pulsed Drain Current $\textcircled{1}$	390	
$P_D @ T_C = 25^\circ C$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current $\textcircled{1}$	62	A
E_{AR}	Repetitive Avalanche Energy $\textcircled{1}$	20	mJ
dv/dt	Peak Diode Recovery dv/dt $\textcircled{3}$	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

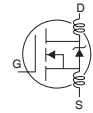
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	8.0	mΩ	$V_{GS} = 10V, I_D = 62A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	44	—	—	S	$V_{DS} = 25V, I_D = 62A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	146	nC	$I_D = 62A$
Q_{gs}	Gate-to-Source Charge	—	—	35		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	54		$V_{GS} = 10V$, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	101	—		$I_D = 62A$
$t_{d(off)}$	Turn-Off Delay Time	—	50	—		$R_G = 4.5\Omega$
t_f	Fall Time	—	65	—		$V_{GS} = 10V$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	3247	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	781	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	211	—		$f = 1.0MHz$, See Fig. 5
E_{AS}	Single Pulse Avalanche Energy ②	—	1050 ⑥	264 ⑦	mJ	$I_{AS} = 62A, L = 138\mu H$



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	390		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 62A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	69	104	ns	$T_J = 25^\circ\text{C}, I_F = 62A$
Q_{rr}	Reverse Recovery Charge	—	143	215	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}, L = 138\mu H$
 $R_G = 25\Omega, I_{AS} = 62A$. (See Figure 12)
- ③ $I_{SD} \leq 62A, di/dt \leq 207A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑥ This is a typical value at device destruction and represents operation outside rated limits.
- ⑦ This is a calculated value limited to $T_J = 175^\circ\text{C}$.

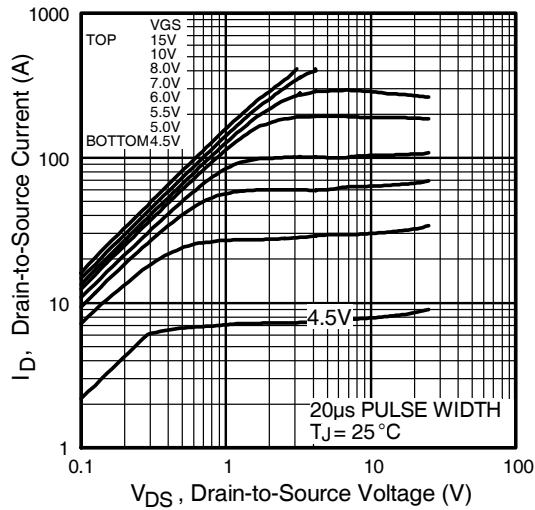


Fig 1. Typical Output Characteristics

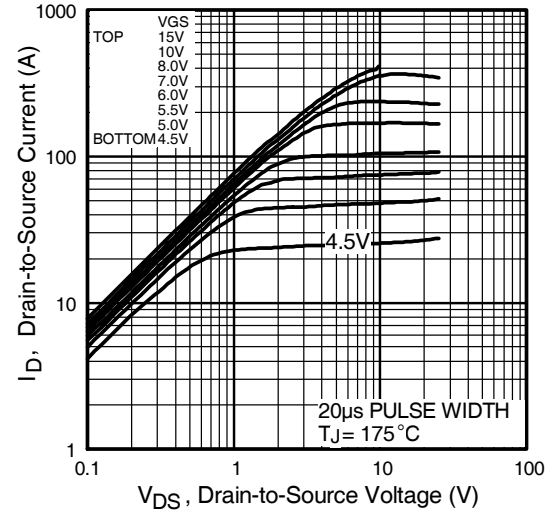


Fig 2. Typical Output Characteristics

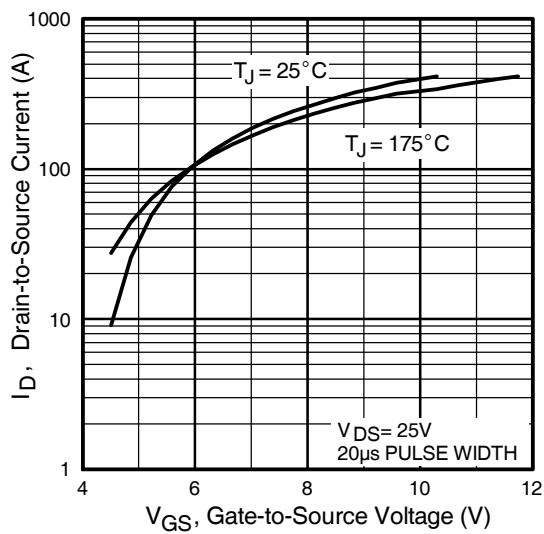


Fig 3. Typical Transfer Characteristics

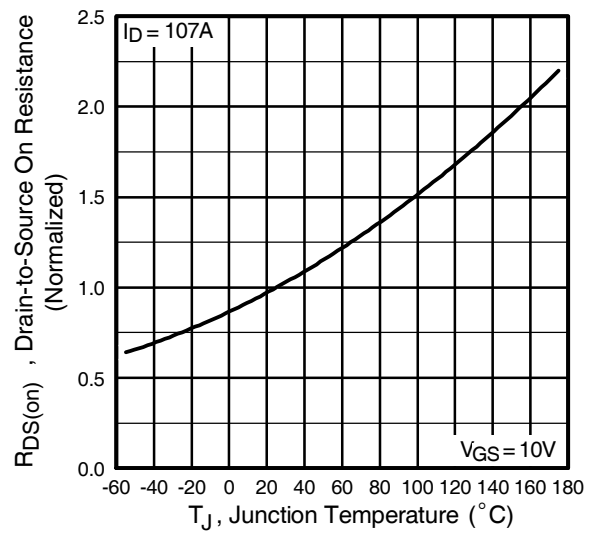
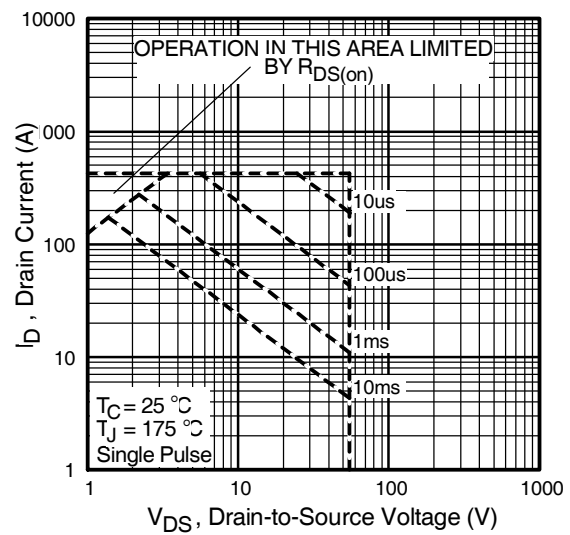
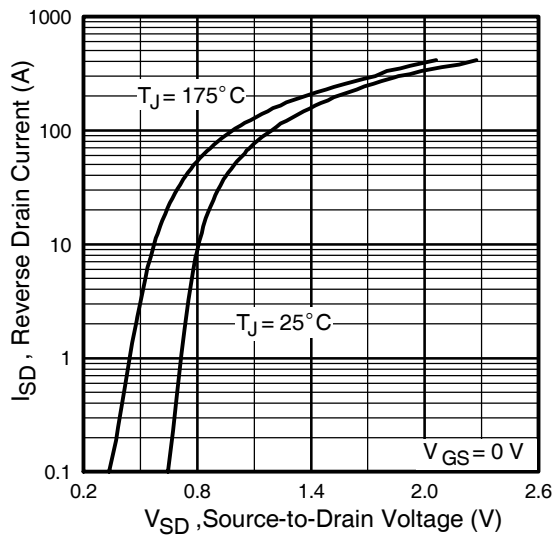
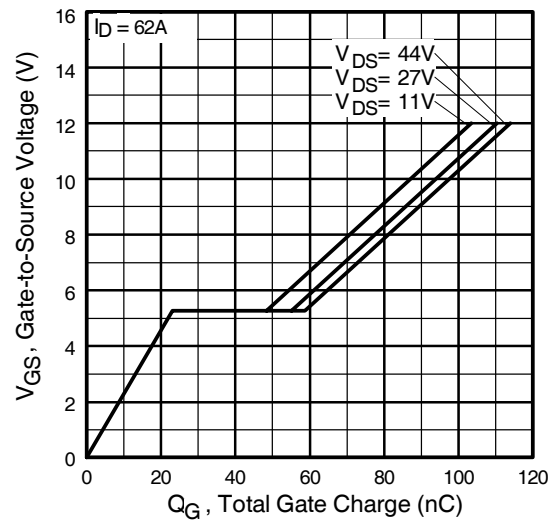
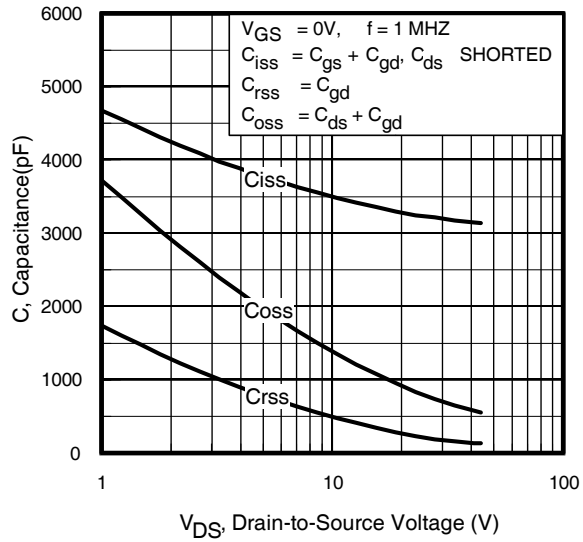


Fig 4. Normalized On-Resistance
Vs. Temperature

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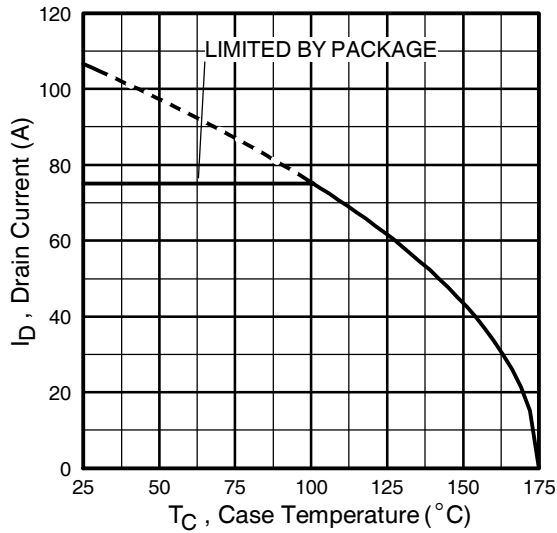


Fig 9. Maximum Drain Current Vs. Case Temperature

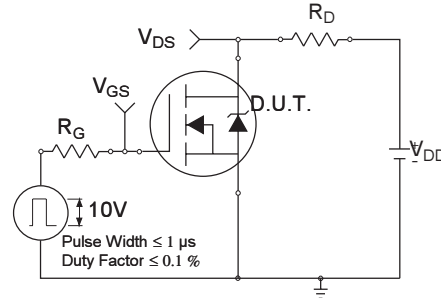


Fig 10a. Switching Time Test Circuit

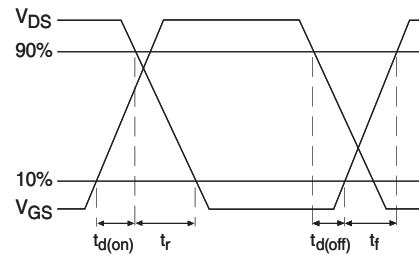


Fig 10b. Switching Time Waveforms

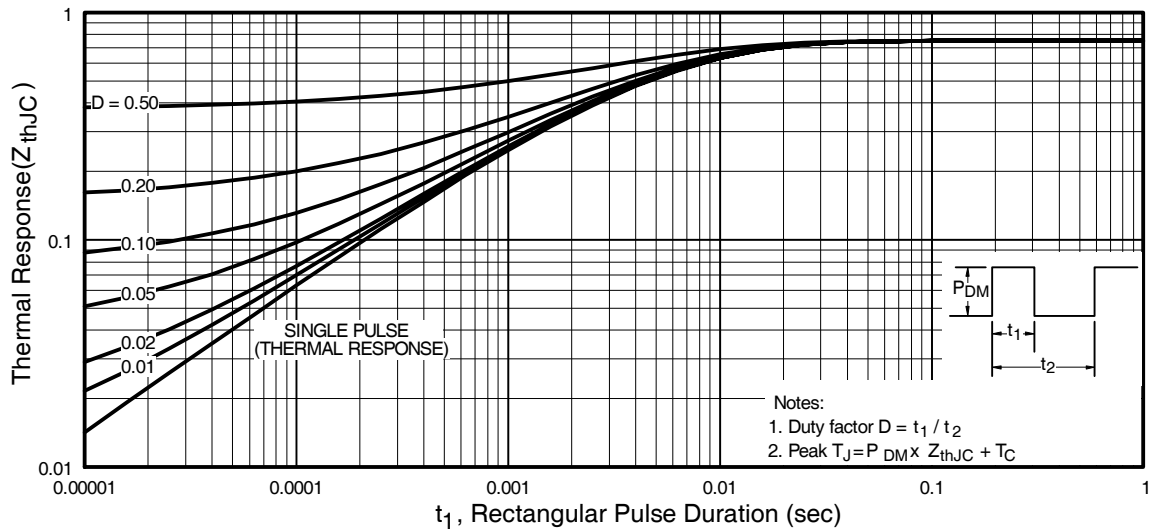


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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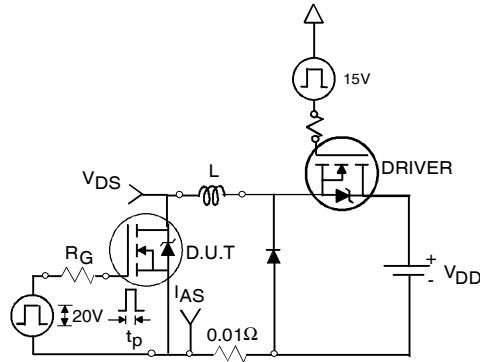


Fig 12a. Unclamped Inductive Test Circuit

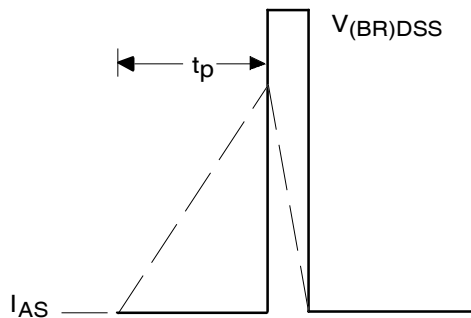


Fig 12b. Unclamped Inductive Waveforms

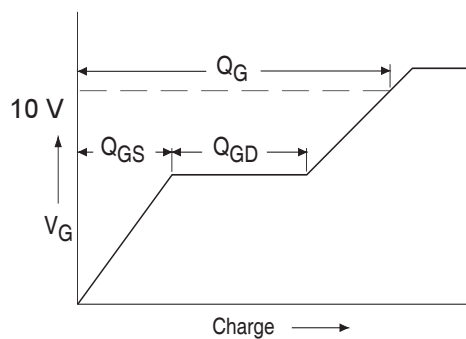


Fig 13a. Basic Gate Charge Waveform

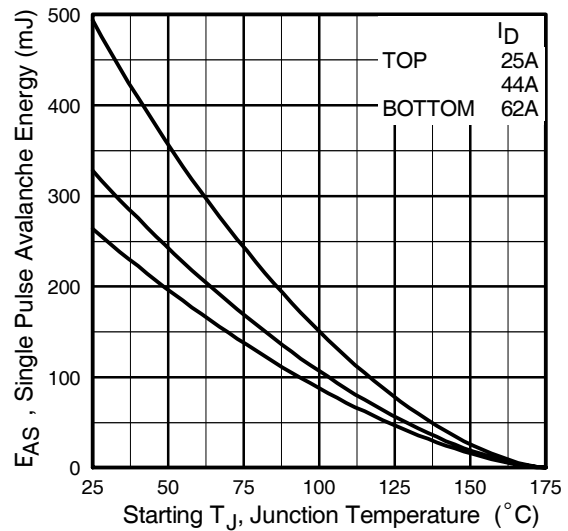


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

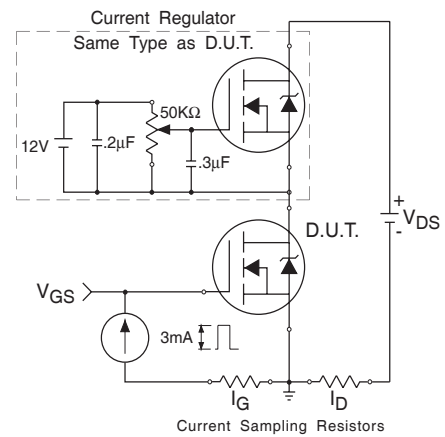


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

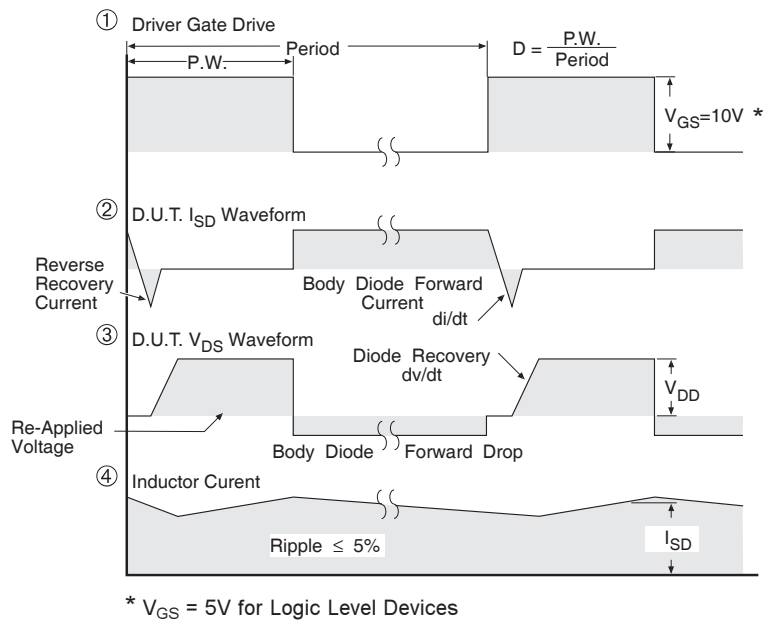
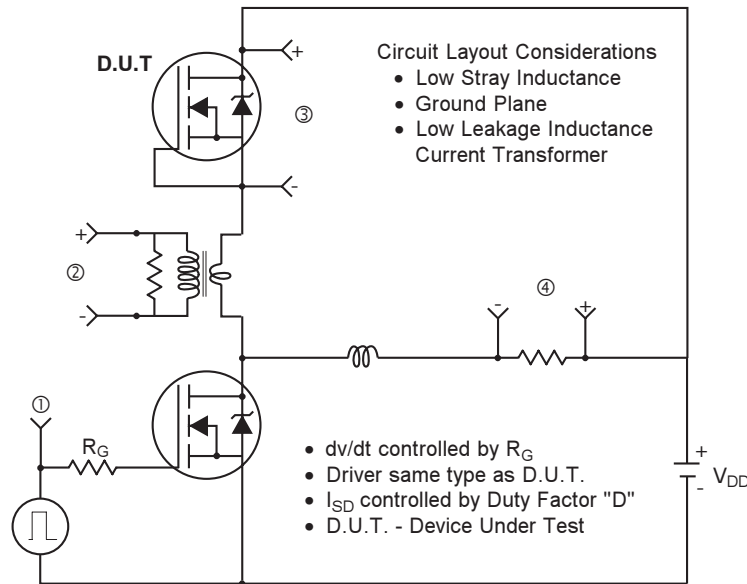


Fig 14. For N-Channel HEXFETS

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Dimensions are shown in millimeters (inches)

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	WFL	THICK	WFL	THICK	
A1	0.56	4.83	1/40	190	
A1	0.91	1.40	.030	.020	
A2	2.03	2.92	.080	.115	
B	0.38	1.01	.015	.038	
C	0.38	0.97	.015	.038	5
D	1.14	1.78	.045	.070	
E	1.14	1.73	.045	.068	
F	0.36	0.81	.014	.032	
G	0.36	0.86	.014	.034	
H	2.22	16.51	.086	.650	4
I1	0.86	9.02	.030	.350	
I2	11.68	12.88	.460	.507	
J	10.55	10.67	.410	.420	7, 7.1
K	6.86	8.89	.270	.350	7
E2	-	-.76	-	-.030	8
	$\frac{1}{16}$ IN. $\frac{1}{8}$ IN. $\frac{1}{4}$ IN. $\frac{1}{2}$ IN. 1 IN.				
L	3.64	6.86	.220	.270	7.8
M	12.70	14.73	.500	.580	
N	3.56	4.06	.140	.160	5
O	3.54	4.06	.139	.161	
P	3.54	3.42	.100	.135	

1-452X

Diagram of an IRF1010 MOSFET package with the following labels:

- INTERNATIONAL RECTIFIER LOGO (points to the IR logo)
- PART NUMBER (points to IRF1010)
- DATE CODE (points to 019C)
- YEAR 0 = 2000
- WEEK 19
- LINE C
- ASSEMBLY LOT CODE (points to 17 89)

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Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd
Minhang District, Shanghai , China

➤ Sales :

Direct +86 (21) 6401-6692
Email amall@ameya360.com
QQ 800077892
Skype ameyasales1 ameyasales2

➤ Customer Service :

Email service@ameya360.com

➤ Partnership :

Tel +86 (21) 64016692-8333
Email mkt@ameya360.com